

Stability of Ge-related point defects and complexes in Ge-doped SiO<sub>2</sub>

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We analyze Ge-related defects in Ge-doped SiO<sub>2</sub> using first-principles density functional techniques. Ge is incorporated at the level of 1 mol% and above. The growth conditions of GeSiO<sub>2</sub> naturally set up oxygen deficiency, with vacancy concentration increasing by a factor 10<sup>5</sup> over undoped SiO<sub>2</sub>, and O vacancies binding strongly to Ge in purities. All the centers considered exhibit potentially EPR-active states, candidates for the identification of the Ge(n) centers. Substitutional Ge produces an apparent gap shrinking via its extrinsic levels.

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Silicon dioxide, besides its role in silicon-based microelectronics, is the central material of fiber optics technology. Germanium doping of silicon dioxide is a key to a number of technologically relevant applications, as e.g. low-loss and modulated-refraction fibers. Ge can be introduced in SiO<sub>2</sub> in concentrations in the 1{10 % range [1]. As is generally true of defects in solids, the identification and characterization of Ge-related defect centers in SiO<sub>2</sub> is a difficult task, and far from completion despite intense recent investigation. This is the case, for instance, for the understanding of oxygen-deficient Ge-related centers and the so called Ge(n) [n=0,1,2,3] centers, for which rather disparate models have been proposed. First-principles defects theory [2{4] can play a key role in this context, predicting the stability regimes and concentrations of Ge and related defects in SiO<sub>2</sub>, and their extrinsic electronic levels and potential magnetically active states. Recently, for example, these techniques were used to pinpoint the correlation of the E<sup>0</sup> center in SiO<sub>2</sub> with the singly-charged O vacancy [2] and the role of hydrogen in determining the leakage current across thin silica layers [3].

Using a similar methodology, here we study the energetics, extrinsic levels, and solubility of Ge in SiO<sub>2</sub>. We predict experimental signatures of a selection of Ge-related defects, including Ge-oxygen vacancy complexes in various stable and metastable configurations and charge states. We demonstrate that oxygen stoichiometry occurs naturally in Ge-doped SiO<sub>2</sub>, and specifically that oxygen deficiency (i.e. O vacancy formation) occurs preferentially near substitutional Ge<sub>Si</sub> sites. The electronic structure of Ge<sub>Si</sub> may explain the observed effective reduction of the gap in Ge-doped silica [5]. Single and paired substitutional Ge and their complexes with an O vacancy are all found to have accessible paramagnetic states: Ge<sub>Si</sub>, and the Ge<sub>Si</sub>-Ge<sub>Si</sub> or Ge<sub>Si</sub>-V<sub>O</sub>-Ge<sub>Si</sub> complexes, are candidates, respectively, for the Ge(1) and Ge(2) electron-capturing centers; two metastable E<sup>0</sup>-like Ge-related centers correlate with the Ge(3) hole center.

Our method can be summarized as follows. The equilibrium concentration of a defect D=

$N_s \exp(-F_{\text{form}}/k_B T_g)$  is determined by the growth temperature  $T_g$ , the number  $N_s$  of available sites, and the formation free energy  $F_{\text{form}} = E_{\text{form}} - TS_{\text{form}}$ . The latter depends [6] on the chemical potentials of atoms added or removed, on the defect charge state, i.e. the charge released to or captured from the electrons reservoir made up by the whole crystal. Given the formation energies of the relevant defects, the concentrations and the electron chemical potential  $\mu_e$  are determined self-consistently to satisfy charge neutrality, as detailed in [6]. A specific defect configuration or charge state is predicted to exist if its formation energy is lower than that of all other defect states for some value of  $\mu_e$ , or when a sufficiently high energy barrier prevents its disappearance. The formation energy for a defect in charge state  $Q$  can be written as

$$E_{\text{form}}^Q = E_{\text{def}}^Q + Q\mu_e + M(Q)(n_{\text{Si}}\mu_{\text{Si}} - n_{\text{Ge}}\mu_{\text{Ge}} - n_{\text{O}}\mu_{\text{O}});$$

where  $E_{\text{def}}^Q$  is the total energy of the defected system in charge state  $Q$ ,  $\mu_e$  the electron chemical potential (equaling the Fermi level  $E_F$  in our  $T=0$  calculations), and  $M(Q)$  a defect- and charge state-dependent multipole correction [7,8]. The  $n_{\text{Si}}$ ,  $n_{\text{Ge}}$  and  $n_{\text{O}}$  atoms considered in the modeling of a specific defect, possess the chemical potentials  $\mu_{\text{Si}}$ ,  $\mu_{\text{Ge}}$ , and  $\mu_{\text{O}}$ , discussed further below.

Energies and forces are calculated from first-principles within density-functional theory in the local approximation, using the ultrasoft pseudopotential plane-wave method as implemented in the VASP code [8]. An isolated defect is simulated in periodic boundary conditions via repeated tetragonal 71{ and 72{atom supercells of crystalline  $\alpha$ -quartz SiO<sub>2</sub> having the (theoretical) linear dimensions 18.49, 16.02, and 20.44 atomic units. Atomic geometries are optimized for all  $Q$ s (which are modeled by removing or adding electrons as appropriate, the added charge being compensated by a uniform background) until all residual force components in the system are below 0.01 eV/Å. No symmetry restriction is imposed. A (222) Monkhorst-Pack mesh is used [8] for  $k$ -space summation (4 points in the supercell Brillouin zone). Total energy differences of different charge

states define ionization energies, i.e. the energy needed to promote e.g. an electron from the valence band into an empty acceptor level. Formation entropies are beyond the scope of the methods used here; plausible estimates are used when needed.

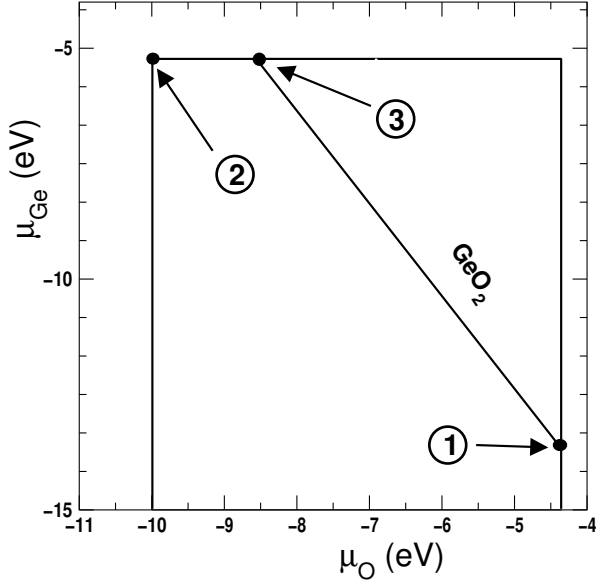


FIG. 1. Solubility region of Si-substituting Ge in  $\text{SiO}_2$  as a function of the impurity and oxygen chemical potentials. Relevant limiting values of the latter are indicated, numbered as in the text. The oblique line is the solubility limit due to  $\text{GeO}_2$  formation. The limit given by  $\text{GeO}$  formation is irrelevant and is not displayed.

To determine the formation energy of Ge and related defects, we must discuss the thermodynamical growth conditions of Ge-doped  $\text{SiO}_2$ . The chemical potentials fall within a range determined by the energy  $\mu_{\text{bulk}}$  of the condensed phase of each atom (bulk oxygen is assumed to be the oxygen molecule), and the calculated formation enthalpies  $H^{\text{SiO}_2} = \{11.31 \text{ eV of } \text{SiO}_2 \text{ and } H^{\text{GeO}_2} = \{8.80 \text{ eV of } \text{GeO}_2\}$ , the most stable compounds liable to form out of O, Si, and Ge. The following conditions apply:

$$\begin{aligned} \mu_{\text{Si}}^{\text{bulk}} + \frac{1}{2} H^{\text{SiO}_2} &= \mu_{\text{Si}}^{\text{bulk}}; \\ \mu_{\text{O}}^{\text{bulk}} + 0.5 H^{\text{SiO}_2} &= \mu_{\text{O}}^{\text{bulk}}; \\ \mu_{\text{Si}} + 2 \mu_{\text{O}} &= \mu_{\text{SiO}_2}^{\text{bulk}}; \quad \mu_{\text{Ge}} + 2 \mu_{\text{O}} = \mu_{\text{GeO}_2}^{\text{bulk}} \end{aligned}$$

The relevant extremal conditions are then

1. O-rich, Si- and Ge-lean:  $\mu_{\text{O}} = \mu_{\text{O}}^{\text{bulk}}$ ,  $\mu_{\text{Si}} = \mu_{\text{Si}}^{\text{bulk}} + \frac{1}{2} H^{\text{SiO}_2}$  and  $\mu_{\text{Ge}} = \mu_{\text{Ge}}^{\text{bulk}} + \frac{1}{2} H^{\text{GeO}_2}$ ;
2. Ge- and Si-rich, O-lean:  $\mu_{\text{Ge}} = \mu_{\text{Ge}}^{\text{bulk}}$ ,  $\mu_{\text{Si}} = \mu_{\text{Si}}^{\text{bulk}}$ , and  $\mu_{\text{O}} = \mu_{\text{O}}^{\text{bulk}} + 0.5 H^{\text{SiO}_2}$ ;
3. Ge-rich, O-lean with respect to  $\text{GeO}_2$ , and Si intermediate:  $\mu_{\text{Ge}} = \mu_{\text{Ge}}^{\text{bulk}}$ ,  $\mu_{\text{Si}} = \mu_{\text{Si}}^{\text{bulk}} + \frac{1}{2} H^{\text{SiO}_2}$ , and  $\mu_{\text{O}} = \mu_{\text{O}}^{\text{bulk}} + 0.5 H^{\text{GeO}_2}$ .

These three cases are indicated in Fig. 1, which depicts the solubility region of Ge in  $\text{SiO}_2$  in the  $\mu_{\text{O}}, \mu_{\text{Ge}}$  plane.

To substitute as much Si as possible with Ge, one should work in comparatively Ge-rich and Si-lean conditions. Case 3 above, the most favorable in this respect, demands at the same time that O be lean with respect to  $\text{GeO}_2$  formation. As a consequence, the material will contain both a high Ge concentration, and a large amount of oxygen deficient centers (as shown below, these tend to localize near Ge atoms). The minimum formation energy of  $\text{Ge}_{\text{Si}}$ , 0.88 eV, is obtained indeed in case 3 above. The ensuing solubility of Ge at a typical growth temperature  $T_g = 1700 \text{ K}$  (which we assume throughout) is 0.2 mol%. This encouragingly high value falls well within the experimental range assuming a plausible formation entropy of  $3.4 k_B$ .

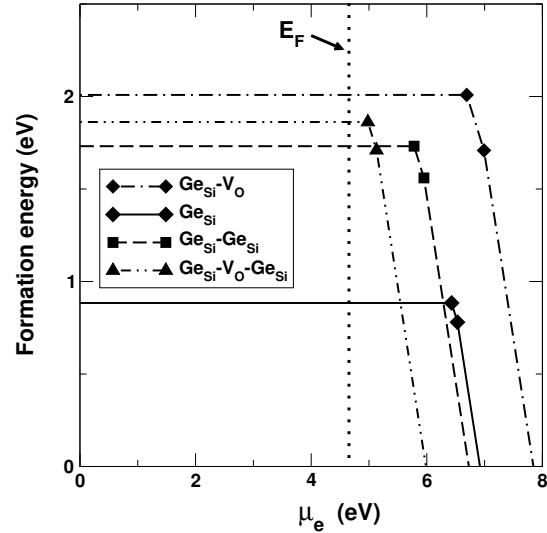


FIG. 2. Formation energy of Ge-related defects:  $\text{Ge}_{\text{Si}}$ , Ge-adjacent oxygen vacancy, substitutional Ge pair with and without O vacancy. The slope of the formation energies is equal to the charge state (possible values are 0, 1, and 2 in the present case). The vertical dotted line indicates the calculated Fermi level. All the centers possess accessible paramagnetic ( $Q = \{1\}$ ) states.

Fig 2 shows the formation energies in various charge states, as a function of the Fermi level and for the growth conditions discussed above, of all the centers considered here, and discussed in turn below: substitutional  $\text{Ge}_{\text{Si}}$ , the oxygen vacancy  $V_{\text{O}}$  adjacent to  $\text{Ge}_{\text{Si}}$ , the  $\text{Ge}_{\text{Si}}\text{-Ge}_{\text{Si}}$  pair (substituting the central Si of two neighboring tetrahedra), the  $\text{Ge}_{\text{Si}}\text{-V}_{\text{O}}\text{-Ge}_{\text{Si}}$  complex (the oxygen bridging the Ge-Ge pair is missing). The dotted vertical line marks the Fermi level as calculated in the presence of all the various defects, namely  $E_F = E_v + 4.65 \text{ eV}$  at room temperature. We assumed a gap of 9 eV, and the band edge effective masses  $m_v' \approx 10 m_e$  and  $m_c' \approx 0.3 m_e$  as estimated in Ref. [9]. Indeed, all the defects considered are in their neutral state at room temperature.

$\text{Ge}_{\text{Si}}$  is neutral over most of the Fermi level range, and captures electrons in strong n-type conditions. Structurally, neutral  $\text{Ge}_{\text{Si}}$  is relatively trivial, with Ge-O bonds (unsurprisingly slightly longer, 1.67 and 1.68 Å, than the bulk Si-O bonds of 1.58 and 1.59 Å) and the other structural parameters (Ge-Si distance: 3.09 Å, O-Ge-O angle: 109°, and Ge-O-Si angle: 142°) being characteristic of an isotropically expanded but otherwise regular tetrahedron. The charge state  $Q = \{1, \text{one of the models proposed [4] for the paramagnetic Ge(1) center, is not stable in the as-grown material, but it may be observed in n-type or electron-irradiated material. Upon electron capture, the Ge substitutional moves to a center causing an orthorhombic distortion with two short and two long Ge-O bonds (differing by 0.2 Å), in good agreement with the report of Ref. [4].$

The properties of  $\text{Ge}_{\text{Si}}$  also match the main Ge-related optical signature in highly doped samples, namely the apparent reduction of the absorption gap to about 7 eV [5]. Indeed, our calculated concentration and electronic structure predict an absorption into the  $\text{Ge}_{\text{Si}}$  extrinsic level starting around 6.5–6.8 eV with an effective valence density of states (DOS) of about  $10^{20} \text{ cm}^{-3}$ . Assuming an impurity band width of 1 eV, likely to occur at such high Ge concentrations, it appears that the valence-to- $\text{Ge}_{\text{Si}}$  extrinsic state is as relevant as the fundamental interband transition, even accounting for reduced oscillator strength, since the effective conduction band DOS of  $\text{SiO}_2$  is in fact about  $1 \cdot 10^{19} \text{ cm}^{-3}$  at room temperature. In summary, the large absorption red shift in  $\text{GeSiO}_2$  is impurity-related, as opposed to a standard alloying effect; a simple  $\text{Si}_{1-x}\text{Ge}_x\text{O}_2$  alloying picture would predict (the gap of  $\text{GeO}_2$  being 5.6 eV) a shift of less than 0.1 eV instead of the observed 2 eV at the typical Ge concentration  $x \approx 0.02$ . The behavior just discussed is similar to the impurity-level (or band) effects observed e.g. in InGaAsN at low N concentration [10].

We now turn to  $V_{\text{O}}$ -Ge centers. The isolated oxygen vacancy at the chemical potentials giving maximum Ge incorporation, has a formation energy of 3.31 eV, i.e. 0.4 eV less than in pure  $\text{SiO}_2$  in stoichiometric conditions. At  $T_g = 1700 \text{ K}$ , this implies a concentration increase of a mere factor of 10. A vacancy in the same simulation cell, but as far as possible from  $\text{Ge}_{\text{Si}}$  (about 7 Å away) has the same formation energy, i.e. it is effectively decoupled from the Ge substitution. However, when the vacancy and  $\text{Ge}_{\text{Si}}$  are first neighbors, the formation energy drops to 2.0 eV (Fig. 2), implying a large attraction for vacancies towards  $\text{Ge}_{\text{Si}}$  centers. Now this reduced formation energy implies that the concentrations of Ge-coupled vacancies is about  $10^4$  that of distant vacancies, and  $10^5$  that of those in pure  $\text{SiO}_2$ , in quantitative agreement with the observed ratio [11]. Therefore the growth conditions of Ge-doped  $\text{SiO}_2$  naturally produce an off-stoichiometry of oxygen: Ge-doped  $\text{SiO}_2$  contains of the order of  $10^5$  more "simple" oxygen deficient centers than

pure  $\text{SiO}_2$  does. In addition this oxygen deficiency is Ge-biased: almost all of the vacancies are localized near  $\text{Ge}_{\text{Si}}$  sites, due to the attractive  $\text{Ge}_{\text{Si}}$ -vacancy effective interaction, and to a lesser extent to the different solubility limits provided by  $\text{GeO}_2$  and  $\text{SiO}_2$ . This applies also, as discussed further below, to the vacancy bridging a pair of Si-substituting Ge.

The ground state of the Ge-neighboring vacancy  $V_{\text{O}}$  {  $\text{Ge}_{\text{Si}}$  is neutral and unpuckered (i.e. the cations neighboring the vacancy remain near the vacant site, and do not undergo distortions of the type involved in the  $E^0$  center [2]. It captures electrons only for extreme n-conditions. The unpuckered +1 charge state is never thermodynamically stable, which rules out, e.g., the possibility of associating this defect to the Ge(0) or Ge(1) centers [1,12]. Instead, similarly to the undoped case [2],  $V_{\text{O}}^+$  becomes a metastable ground state in a puckered configuration (lower than the unpuckered one by 0.15 eV) if the Fermi level is below about 1.6 eV [13]. Thereby, it may be a candidate for the Ge(3) center [1,14,15]. The  $E^0$ -like off-site puckering involves the Si atom adjacent to the vacancy, since the puckering of Ge (on the correct side of the vacancy [2]) costs 1.3 eV more than that of Si. Consequently, the  $\text{Ge}_{\text{Si}}$  is left with an EPR-detectable unpaired electron, in agreement with the fact that the EPR lines of Ge(3) show [16] the characteristic signatures of hyperfine interaction with  $^{73}\text{Ge}$ .

Given the larger amount of vacancies and their preference for the vicinities of Ge, and accounting for the  $^{73}\text{Ge}$  and  $^{29}\text{Si}$  isotopic abundances of 8% and 4%, the concentration of Si-Ge  $E^0$  measured by EPR should be a factor of  $10^4$  that of  $E^0$  in  $\text{SiO}_2$ . Observed values [17] are in a range upwards of  $10^2$ . In agreement with the observed axial symmetry of Ge(3), the bond lengths between the EPR-active Ge and the three first-neighbor oxygens are about the same. Also, the fact that the puckered configuration is lower in energy than the unpuckered one agrees with the observation of Ge(3) defects even in non-irradiated samples [1].

As mentioned, the thermodynamical stability of Si-Ge  $E^0$  is possible only at rather extreme p-conditions ( $\mu_e \approx 1.6 \text{ eV}$ ), not realized in as-grown material. This center should therefore be observed only upon (radiation-induced or electrical) hole injection. In as-grown material, it may still be possible that, after its excitation to the positive state by e.g. an optical excitation, the return of Ge-Si  $E^0$  to the neutral (and thence to the unpuckered) state is slowed down due to selection rules and/or disorder, neither of which have been considered here.

So far we identified possible candidates for the Ge(1) electron-capturing and Ge(3)  $E^0$ -like centers. We now move on to Ge-pair defects, consisting of two corner-sharing Ge-centered tetrahedra. In the neutral state, the tetrahedra exhibit Ge-O bonds and angles close to those of the isolated  $\text{Ge}_{\text{Si}}$  in their neutral state.

As seen in Fig. 2, the formation energy of two Ge

impurities at neighboring substitutional sites is almost exactly twice that of isolated  $\text{Ge}_{\text{Si}}$ ; therefore, there is neither a driving force for, nor an energetic hindrance against, the clustering of  $\text{Ge}_{\text{Si}}$ . Kinetics, and hence thermal and growth history will play the deciding role. Once more, the  $Q = \{1\}$  charge state is not a ground state of the defect in as-grown material, but it may be observed in n-doped irradiated material, and thereby become a candidate for the  $\text{Ge}(2)$  paramagnetic center, as suggested in Ref. [18].

Finally we consider the formation of  $V_0$  between the two Ge atoms: it costs 0.15 eV less than between a Ge and a Si (Fig. 2), because of the previously discussed natural tendency of the two Ge to host oxygen nearby them; this gives a concentration of a further factor of 3 higher than for the Ge-neighboring vacancy. In this case, the negative charging level is just slightly ( $\sim 0.1$  eV) above the Fermi level so that, given the uncertainties on the energy levels, it may well turn out to be already occupied in weakly, unintentionally n-type as-grown material, or will readily become occupied in moderately n-doped or irradiated material. Thus  $\text{Ge-V}_0$ -Ge stands out as well as a candidate for the  $\text{Ge}(2)$  paramagnetic center [1].

Once more, the unpuckered +1 vacancy is not a stable ground state; its  $E^0$  like puckered-Ge configuration becomes metastable below  $\epsilon_{\text{F}} = 1.5$  eV [13]. As the metastable energy minimum is found to be 0.45 eV higher than the undistorted one, the EPR-active Ge-pair  $E^0$  like configuration is far less frequent than the Si-Ge one ( $\sim 10^{-7}$  at room temperature, although it is possible that, as for the standard  $E^0$ , a conformational barrier exists prolonging its existence). This suggests that the proposed [11] attribution of the  $\text{Ge}(3)$  center to this complex is unlikely to be correct.

In summary, we have shown that thermodynamical growth conditions of Ge-doped  $\text{SiO}_2$  naturally produce oxygen-stoichiometry of oxygen, and that oxygen deficient centers form preferentially near Ge impurities. We find that energetics is neutral as to clustering of substitutional Ge, so that kinetics will be important. The calculated concentration (in agreement with experiment) and electronic structure of  $\text{Ge}_{\text{Si}}$  show a large density of states starting at 6.5-6.8 eV which may explain the apparent gap reduction to about 7 eV in absorption. Our results contribute to the identification of the  $\text{Ge}(1)$ ,  $\text{Ge}(2)$ , and  $\text{Ge}(3)$  centers.  $\text{Ge}(1)$  and  $\text{Ge}(2)$  are electron-capturing paramagnetic centers; the former is probably related to the singly negative states of  $\text{Ge}_{\text{Si}}$ ; the latter may be associated with the singly-negative  $\text{Ge}_{\text{Si}}\text{-Ge}_{\text{Si}}$  or  $\text{Ge}_{\text{Si}}\text{-V}_0\text{-Ge}_{\text{Si}}$  complexes.  $\text{Ge}(3)$  may instead be attributed to the Ge-Si  $E^0$ -like center. Hyperfine-parameter calculations

are underway to pinpoint these attributions. In any case, these centers should be preferentially observed in n-doped or irradiated material.

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- [1] E. J. Friebele, D. L. Griscom, and G. H. Sigel, *J. Appl. Phys.* **45**, 3424 (1974); E. J. Friebele and D. L. Griscom, in *Defects in Glasses*, edited by E. L. Galoneer, D. L. Griscom, and M. J. Weber (MRS, Pittsburgh, 1985), p. 319.
  - [2] C. M. Carbonaro, V. Fiorentini, and F. Bernardini, *Phys. Rev. Lett.* **86**, 3064 (2001).
  - [3] P. E. Blochl and J. H. Stathis, *Phys. Rev. Lett.* **83**, 372 (1999); P. E. Blochl, *Phys. Rev. B* **62**, 6158 (2000).
  - [4] G. Pacchioni and C. Mazzeo, *Phys. Rev. B* **62**, 5452 (2000).
  - [5] J. Nishii, N. Kitamura, H. Tamamaka, H. Osono, and H. Kawazoe, *Optics Lett.* **20**, 1184 (1995); H. Osono, H. Kawazoe, and J. Nishii, *Phys. Rev. B* **53**, R11921 (1996).
  - [6] C. G. van de Walle, D. B. Laks, G. F. Neumark, and S. T. Pantelides, *Phys. Rev. B* **47**, 9425 (1993).
  - [7] M. Leslie and M. G. Gillan, *J. Phys. C* **18**, 973 (1985); G. Makov and M. C. Payne, *Phys. Rev. B* **51**, 4014 (1995).
  - [8] G. Kresse and J. Furthmüller, *Comput. Mater. Sci.* **6**, 15 (1996); G. Kresse and J. Furthmüller, *Phys. Rev. B* **54**, 11169 (1996); and the web site <http://cms.mpi.univie.ac.at/vasp/>.
  - [9] J. R. Chelikowsky and M. Schluter, *Phys. Rev. B* **15**, 4020 (1977).
  - [10] T. M. Attila, S.-H. Wei, and A. Zunger, *Phys. Rev. B* **60**, R11425 (1999).
  - [11] H. Osono, Y. Abe, D. L. Kinsler, R. A. Weeks, K. Muta, and H. Kawazoe, *Phys. Rev. B* **46**, 11445 (1992).
  - [12] N. Chiodini, F. Meinardi, F. Morazzoni, A. Palcari, and R. Scotti, *Phys. Rev. B* **60**, 2429 (1999).
  - [13] At this energy, the puckered +1 state drops below the puckered neutral; the unpuckered neutral is always lower than unpuckered +1 (see e.g. [2] for more details, in particular Fig. 2).
  - [14] T. Uchino, M. Takahashi, and T. Yoko, *Phys. Rev. Lett.* **84**, 1475 (2000).
  - [15] M. Fujimaki, T. Watanabe, T. Katoh, T. Kasahara, N. Miyazaki, and Y. Ohki, *Phys. Rev. B* **57**, 3920 (1998).
  - [16] T. E. Tsalis, D. L. Griscom, and J. L. Friebele, *J. Appl. Phys.* **62**, 2264 (1987).
  - [17] R. Crivelli, M. Martini, F. Meinardi, A. Palcari, and G. Spinolo, *Phys. Rev. B* **54**, 16637 (1996).
  - [18] H. Kawazoe, *J. Non-Cryst. Solids* **71**, 231 (1985).